

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)	I _D (A)	Q _g (Typ.)			
- 100	185 at V _{GS} = - 10 V	- 3.8	7.9			
- 100	212 at V _{GS} = - 4.5 V	- 3.0	7.9			

FEATURES

- DT-Trench Power MOSFET
- 100 % Rand UIS tested
- Ultra Low On-Resistance



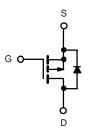
APPLICATIONS

• Active Clamp Circuits in DC/DC Power Supplies





Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS \top	$_{A}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	LIMIT	Unit	
Drain-Source Voltage		V _{DS}	- 100	V	
Gate-Source Voltage	V _{GS}	± 20]		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	- I _D	- 3.8		
Continuous Diam Current (1) = 150°C)	T _A = 70 °C		- 2.5		
Pulsed Drain Current		I _{DM}	- 11	А	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 3.8		
Single Pulse Avalanche Current	L = 1.0 mH	I _{AS}	3.5		
Single Pulse Avalanche Energy	L = 1.0 IIII	E _{AS}	13	mJ	
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	P _D	1.55	W	
waximum Power Dissipation 5, 5	T _A = 70 °C	, p	0.93		
Operating Junction and Storage Temperature Range	е	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^a	t ≤ 5 s	D	70	95			
	Steady State	R_{thJA}	115	150	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	45]		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



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			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 100			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 1.2		- 2.5	v	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaga Brain Current	1	V _{DS} = - 100 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 80 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 3.8			Α	
	D	$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$		0.185	0.240	0.240	
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.5 \text{ A}$		0.212	0.290	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 0.5 A		2.2		S	
Diode Forward Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		0.7	- 1.2	V	
Dynamic ^b			•				
Total Gate Charge	Q_g	V 75 V V 10 V		7.9	13		
Gate-Source Charge	Q _{gs}	$V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$		1.6		nC	
Gate-Drain Charge	Q_{gd}	ID = - 0.5 A		2.5			
Gate Resistance	R _g	f = 1.0 MHz		9		Ω	
Input Capacitance	C _{iss}			350	520		
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		35		pF	
Reverse Transfer Capacitance	C _{rss}			16		1	
Switching ^c							
Turn On Time	t _{d(on)}	V 75 V D 75 0	8	13			
Turn-On Time	t _r	V_{DD} = - 75 V, R_L = 75 Ω $I_D \cong$ - 1.0 A, V_{GEN} = - 10 V		11	19	7	
Turn Off Time	t _{d(off)}	$R_{\alpha} = 6 \Omega$		16	26	ns	
Turn-Off Time	t _f	. · · · · · · · · · · · · · · · · · · ·		11	19		
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		90	135	nC	

Notes:

- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %. b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

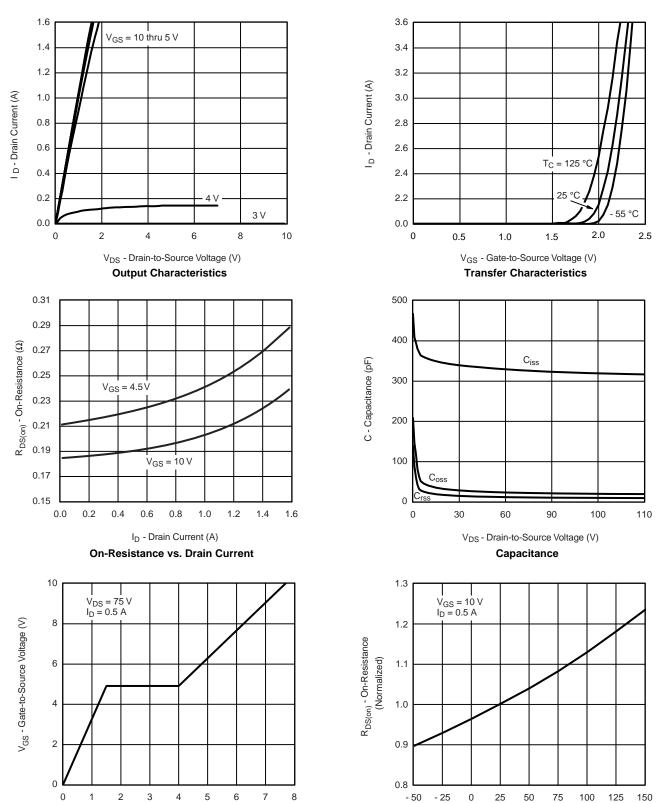


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Q_g - Total Gate Charge (nC)

Gate Charge

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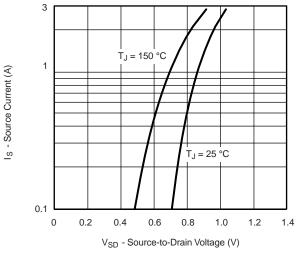


 T_J - Junction Temperature (°C)

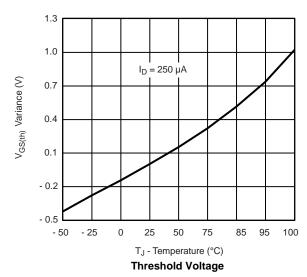
On-Resistance vs. Junction Temperature

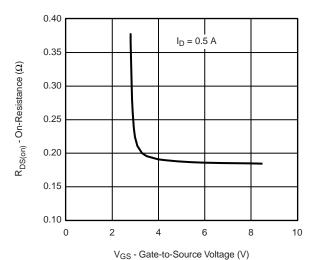


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

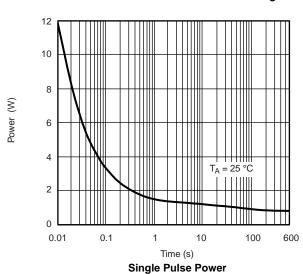


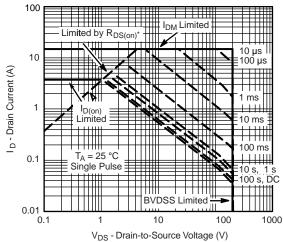
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



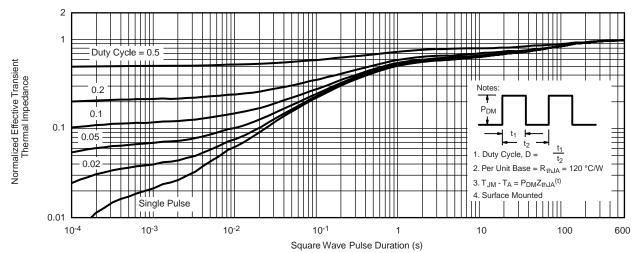


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area



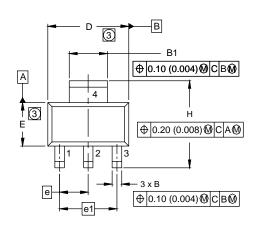
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

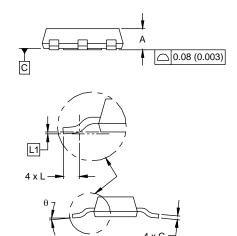


Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-223 (HIGH VOLTAGE)





DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
Α	1.55	1.80	0.061	0.071
В	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
С	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
е	2.30 BSC		0.0905 BSC	
e1	4.60	4.60 BSC		BSC
Н	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024	4 BSC
θ	-	10'	-	10'

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.





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